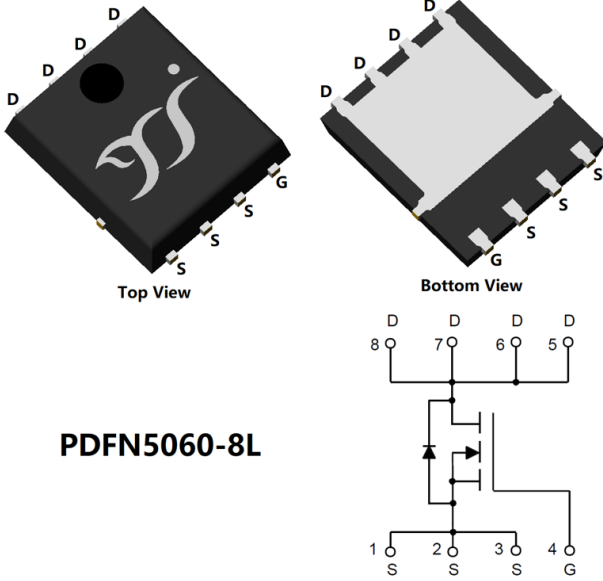


N-Channel Enhancement Mode Field Effect Transistor



PDFN5060-8L

Product Summary

- V_{DS} 100V
- I_D 40A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) $< 19m\Omega$
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) $< 23m\Omega$
- 100% UIS Tested
- 100% ∇V_{DS} Tested

General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Part no. with suffix "Q" means AEC-Q101 qualified

Applications

- Power switching application
- Uninterruptible power supply
- DC-DC convertor

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ C$	I_D	7	A
	$T_A=100^\circ C$		4.5	
	$T_C=25^\circ C$		40	
	$T_C=100^\circ C$		25	
Pulsed Drain Current ^A		I_{DM}	120	A
Avalanche energy ^B		EAS	81	mJ
Total Power Dissipation ^C	$T_A=25^\circ C$	P_D	2.5	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		70	
	$T_C=100^\circ C$		28	
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+150	$^\circ C$



YJG40G10AQ

■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient ^D	Steady-State	R _{θJA}	40	50	°C/W
Thermal Resistance Junction-to-Case	Steady-State	R _{θJC}	1.5	1.8	

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG40G10AQ	F1	YJG40G10A	5000	10000	100000	13" reel



YJG40G10AQ

■ Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
		V _{DS} =100V, V _{GS} =0V, T _J =150°C	-	-	100	
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D =250μA	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	15	19	mΩ
		V _{GS} =4.5V, I _D =20A	-	18	23	
Diode Forward Voltage	V _{SD}	I _S =20A, V _{GS} =0V	-	0.9	1.2	V
Gate resistance	R _G	f=1MHz, Open drain	-	1.4	-	Ω
Maximum Body-Diode Continuous Current	I _S		-	-	40	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz	-	1150	-	pF
Output Capacitance	C _{oss}		-	370	-	
Reverse Transfer Capacitance	C _{rss}		-	8	-	
Switching Parameters						
Total Gate Charge	Q _g	V _{GS} =10V, V _{DS} =50V, I _D =20A	-	17	-	nC
Gate-Source Charge	Q _{gs}		-	6	-	
Gate-Drain Charge	Q _{gd}		-	3	-	
Reverse Recovery Charge	Q _{rr}	I _F =20A, di/dt=100A/us	-	42	-	nC
Reverse Recovery Time	t _{rr}		-	40	-	ns
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =50V, I _D =20A R _{GEN} =2.2Ω	-	40	-	ns
Turn-on Rise Time	t _r		-	12	-	
Turn-off Delay Time	t _{D(off)}		-	55	-	
Turn-off fall Time	t _f		-	16	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T_J=25°C, V_{DD}=50V, V_G=10V, R_G=25Ω, L=2mH, I_{AS}=9A.

C. P_q is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R_{θJA} is measured with the device mounted on the minimum recommend pad size, in the still air environment with T_A =25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



YJG40G10AQ

Typical Electrical and Thermal Characteristics Diagrams

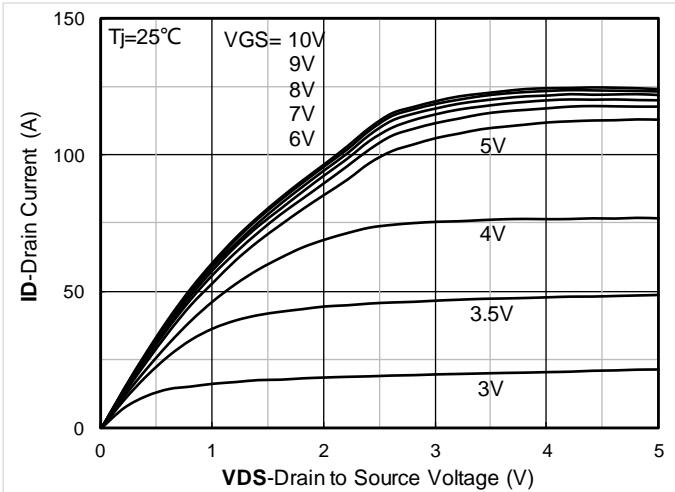


Figure 1. Output Characteristics

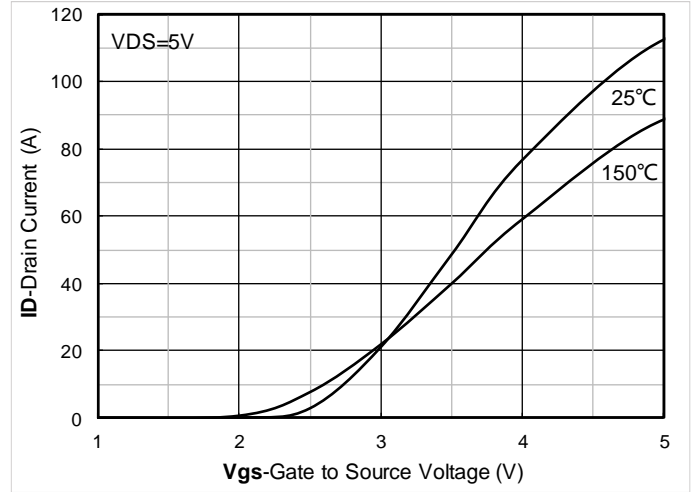


Figure 2. Transfer Characteristics

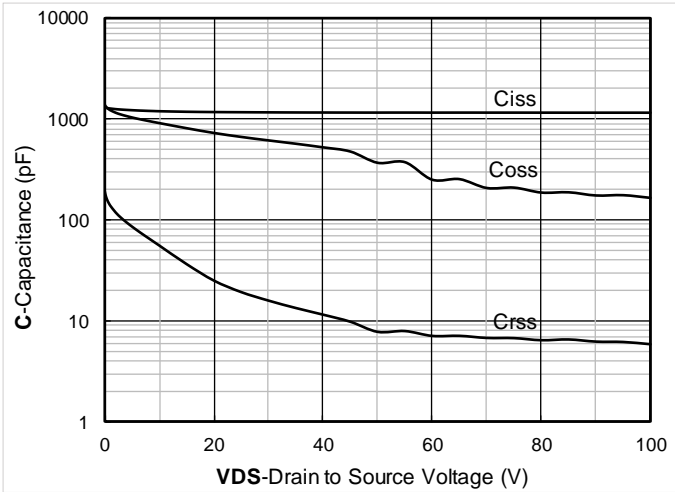


Figure 3. Capacitance Characteristics

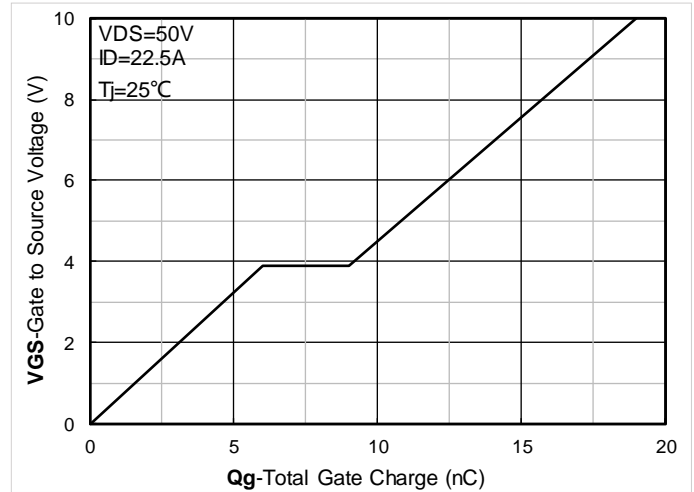


Figure 4. Gate Charge

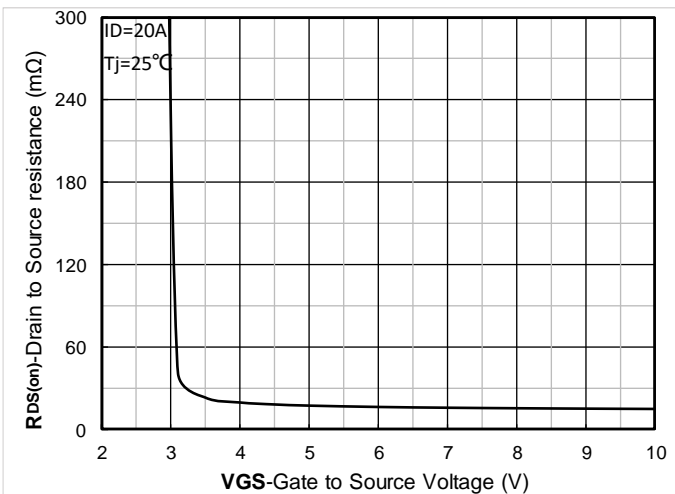


Figure 5. On-Resistance vs Gate to Source Voltage

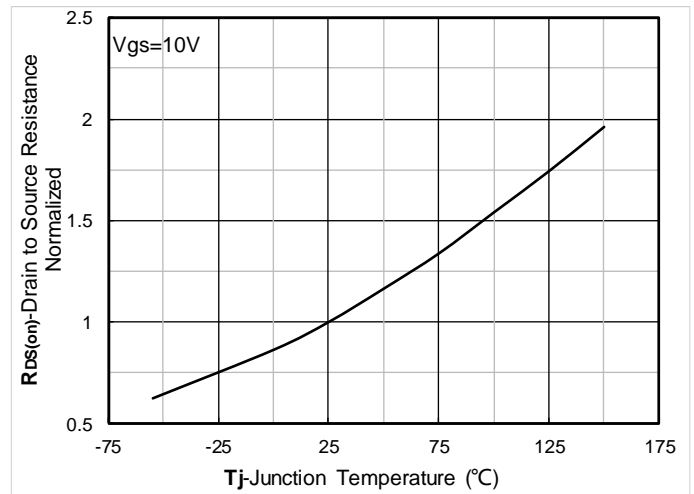


Figure 6. Normalized On-Resistance



YJG40G10AQ

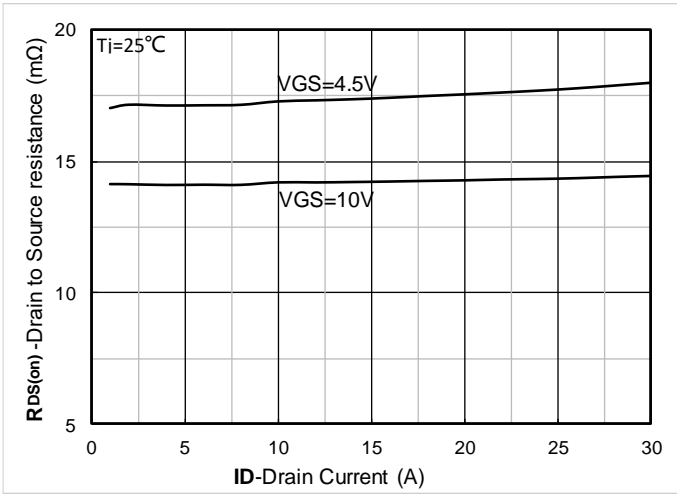


Figure 7. RDS(on) VS Drain Current

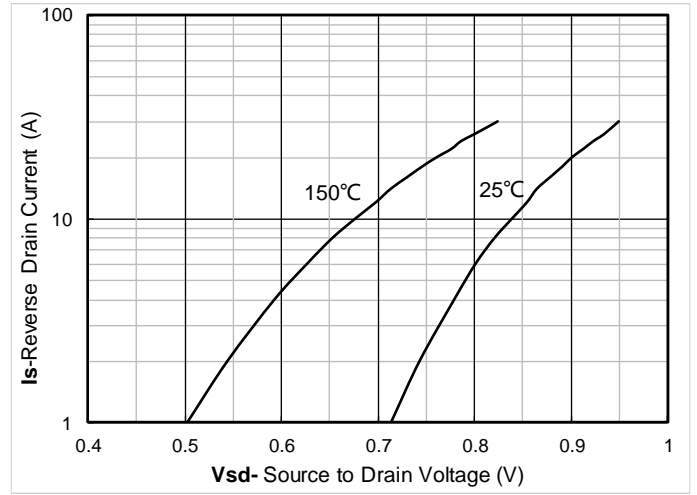


Figure 8. Forward characteristics of reverse diode

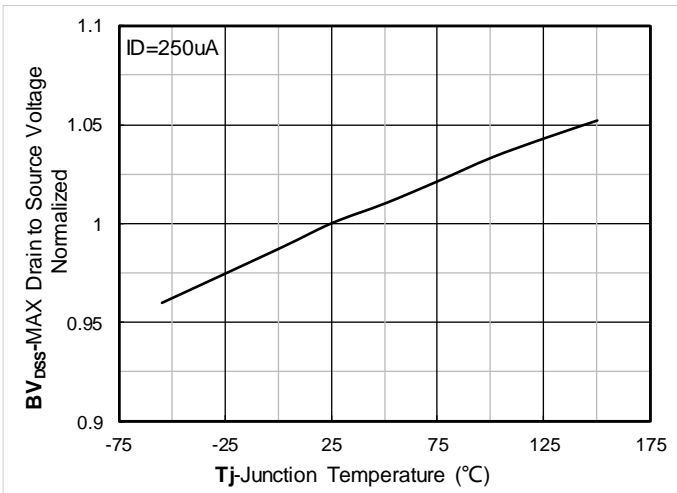


Figure 9. Normalized breakdown voltage

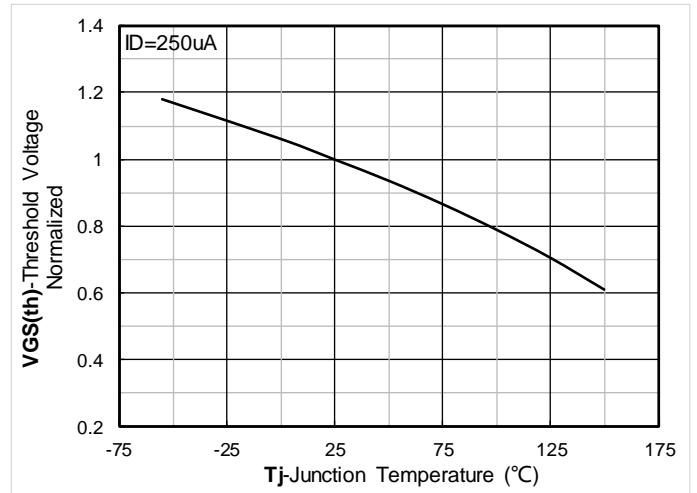


Figure 10. Normalized Threshold voltage

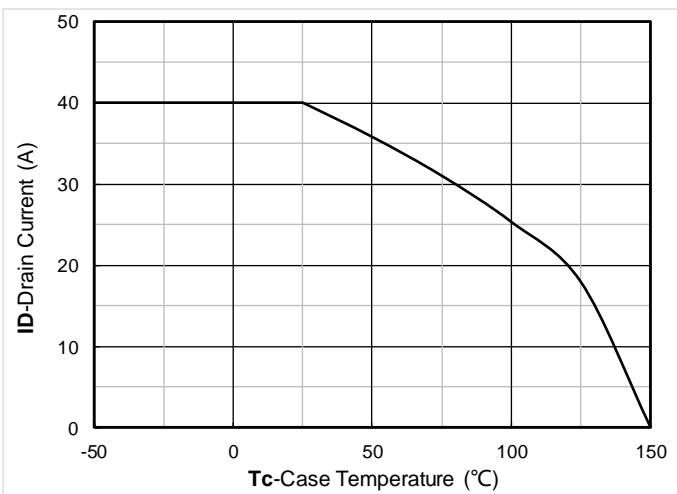


Figure 11. Current dissipation

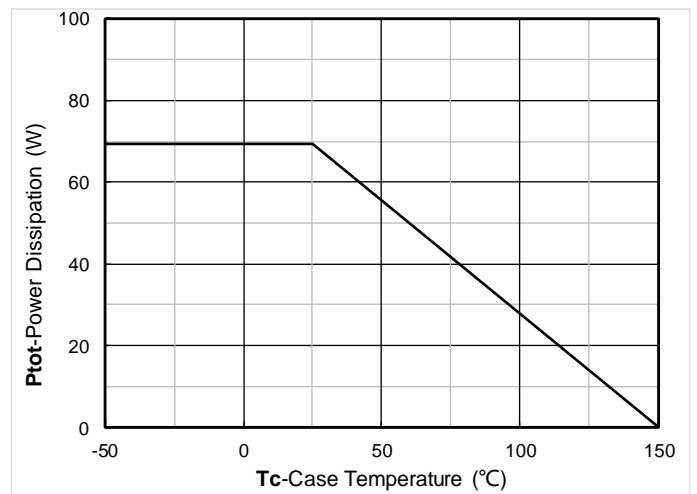


Figure 12. Power dissipation

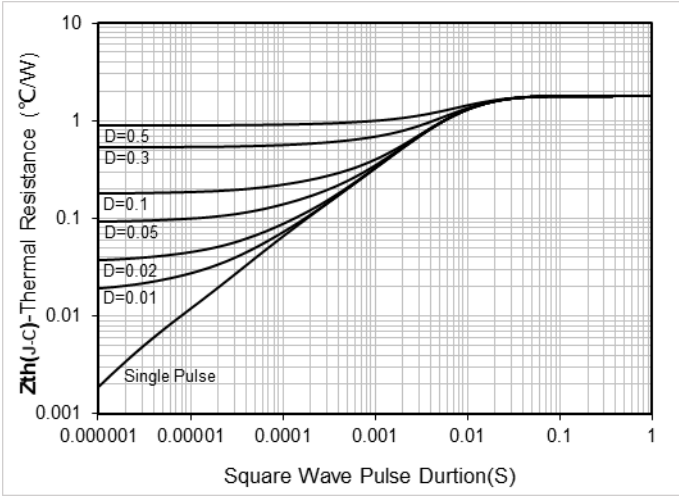


Figure 13. Maximum Transient Thermal Impedance

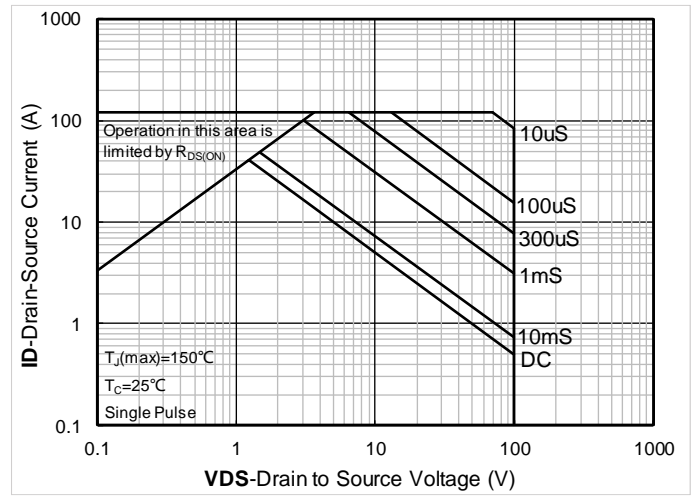


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

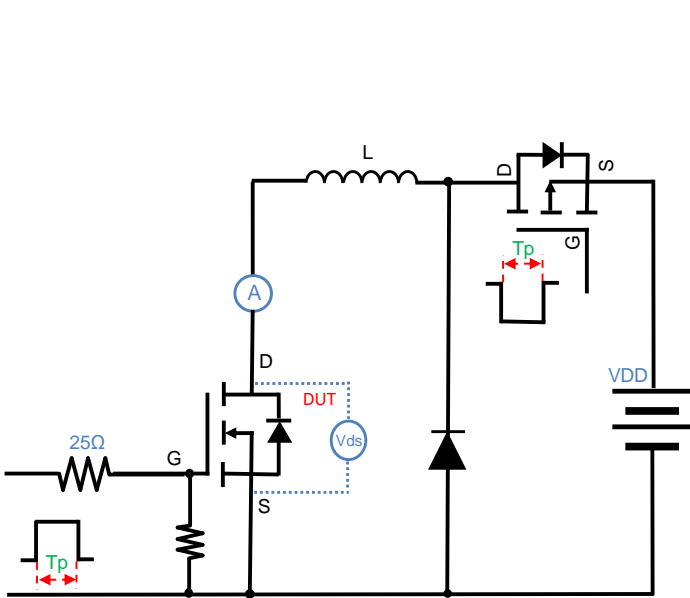
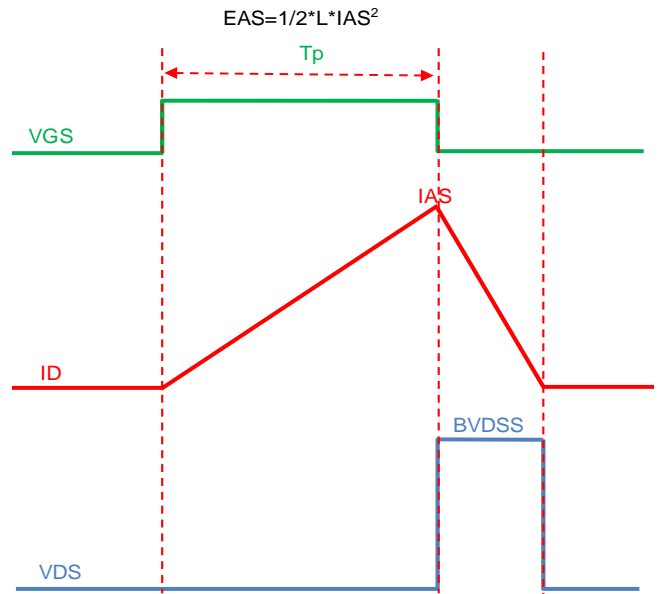


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



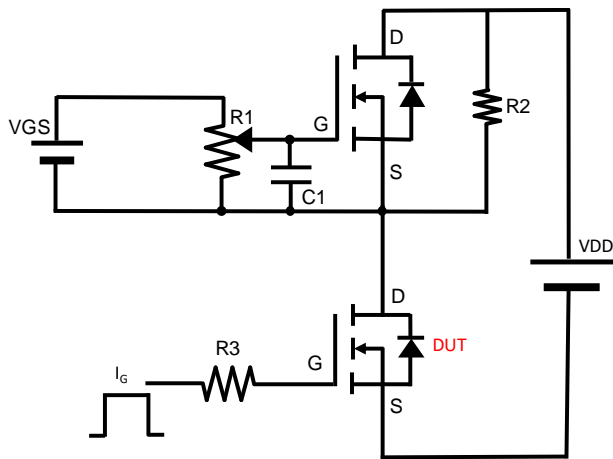


Figure B. Gate Charge Test Circuit & Waveform

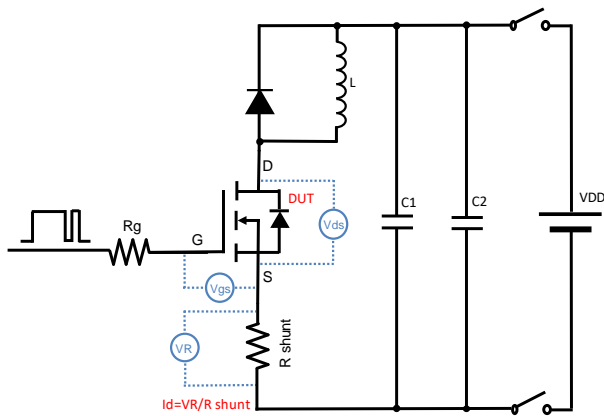


Figure C. Resistive Switching Test Circuit & Waveform

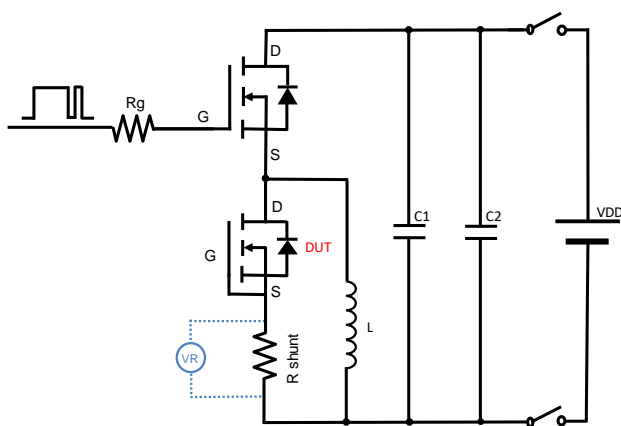
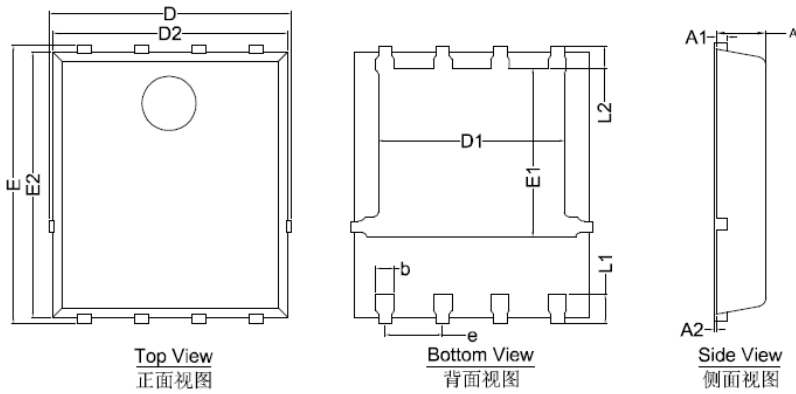


Figure D. Diode Recovery Test Circuit & Waveform

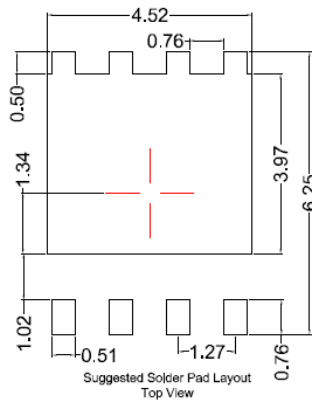


YJG40G10AQ

■ PDFN5060-8L-B-1.1MM Package information



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: ± 0.10 mm.
 3. The pad layout is for reference purposes only.



YJG40G10AQ

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with automotive electronics, are not designed for use in medical, life-saving, lifesustaining, or military, Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.